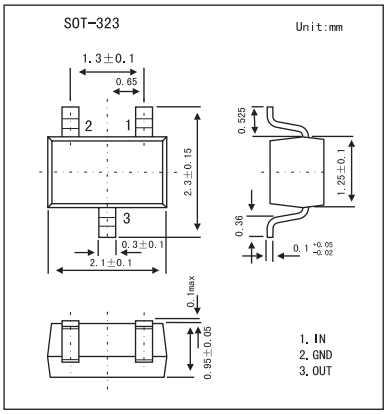
Schottky barrier (double) diodes

1PS70SB10; 1PS70SB14
1PS70SB15; 1PS70SB16



■ Features

- Low forward voltage
- Guard ring protected
- Very small plastic SMD package

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			30	V
Continuous forward current	I_F			200	mA
Repetitive peak forward current	I_{FRM}	$t_p \leqslant 1s, \delta \leqslant 0.5$		300	mA
Non-repetitive peak forward current	I_{FSM}	$t_p < 10$ ms		600	mA
Total power dissipation (per package)	P_{tot}	$T_{amb} < 25$ ℃		200	mW
Storage temperature	T_{stg}		-65	+150	℃
Junction temperature	T_j			125	℃
Operating ambient temperature	T_{amb}		-65	+125	℃
thermal resistance from junction to ambient	$R_{th\ j-a}$			625	K/W

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous forward voltage	V_F	I_F = 0.1 mA		240	mV
		I_F = 1 mA		320	mV
		I_F = 10 mA		400	mV
		I_F = 30 mA		500	mV
		I_F = 100 mA		800	mV
Reverse current	I_R	V_R = 25 V, Note 1	2	15	μA
Diode capacitance	C_d	V_R = 0 V; f = 1 MHz	10	50	pF

Note

1. Pulse test: $t_p < 300$ μs; $\delta \leqslant 0.02$.

■ Marking

Type	1PS70SB10	1PS70SB14	1PS70SB15	1PS70SB16
Marking	7*0	7*4	7*5	7*6